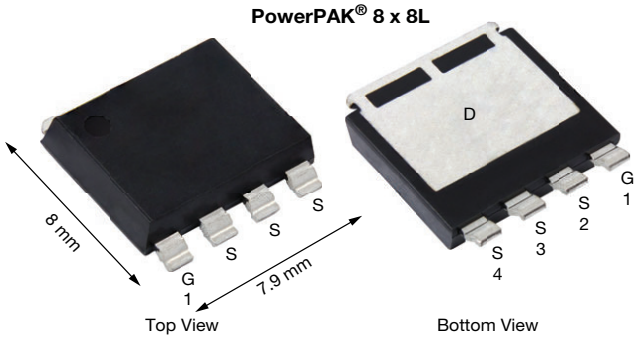
Automotive N-Channel 40 V (D-S) 175 °C MOSFET



FEATURES

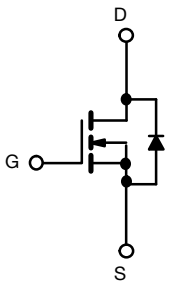
- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Thin 1.6 mm package
- Very low thermal resistance
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

AUTOMOTIVE GRADE

Pb-free

RoHS COMPLIANT

HALOGEN FREE



N-Channel MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	40
$R_{DS(on)}$ (Ω) at V_{GS} = 10 V	0.0019
I_D (A)	233
Configuration	Single
Package	PowerPAK 8 x 8L

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V_{DS}	40	V
Gate-source voltage		V_{GS}	± 20	
Continuous drain current	T_C = 25 °C	I_D	233	A
	T_C = 125 °C		134	
Continuous source current (diode conduction)		I_S	170	
Pulsed drain current [a]		I_{DM}	930	
Single pulse avalanche current	L = 0.1 mH	I_{AS}	38	
Single pulse avalanche energy		E_{AS}	72	mJ
Maximum power dissipation	T_C = 25 °C	P_D	187	W
	T_C = 125 °C		62	
Operating junction and storage temperature range		T_J, T_{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) [c]			260	

THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount [b]	R_{thJA}	44	°C/W
Junction-to-case (drain)		R_{thJC}	0.8	

Notes

a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %

b. When mounted on 1" square PCB (FR4 material)

c. See solder profile (www.vishay.com/doc?73257). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

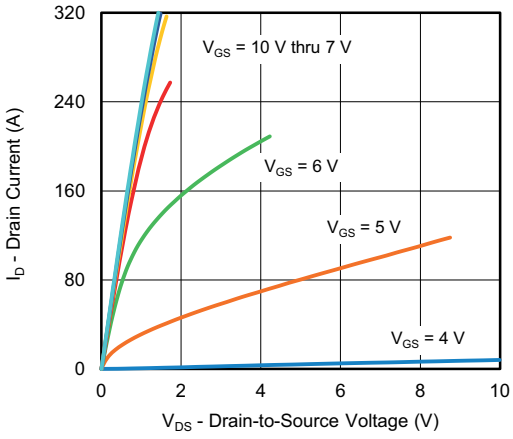
SPECIFICATIONS (T_C = 25 °C, unless otherwise noted)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static							
Drain-source breakdown voltage	V_{DS}	V_{GS} = 0, I_D = 250 µA		40	-	-	V
Gate-source threshold voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA		2	2.8	3.5	
Gate-source leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V		-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	V_{GS} = 0 V	V_{DS} = 40 V	-	-	1	µA
		V_{GS} = 0 V	V_{DS} = 40 V, T_J = 125 °C	-	-	50	
		V_{GS} = 0 V	V_{DS} = 40 V, T_J = 175 °C	-	-	150	
On-state drain current [a]	$I_{D(on)}$	V_{GS} = 10 V	V_{DS} ≥ 5 V	100	-	-	A
Drain-source on-state resistance [a]	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 20 A	-	0.0015	0.0019	Ω
		V_{GS} = 10 V	I_D = 20 A, T_J = 125 °C	-	-	0.003	
		V_{GS} = 10 V	I_D = 20 A, T_J = 175 °C	-	-	0.0035	
Forward transconductance [b]	g_{fs}	V_{DS} = 15 V, I_D = 30 A		-	120	-	S
Dynamic [b]							
Input capacitance	C_{iss}	V_{GS} = 0 V	V_{DS} = 25 V, f = 1 MHz	-	3316	4643	pF
Output capacitance	C_{oss}			-	1137	1592	
Reverse transfer capacitance	C_{rss}			-	134	188	
Total gate charge [c]	Q_g	V_{GS} = 10 V	V_{DS} = 20 V, I_D = 20 A	-	61	92	nC
Gate-source charge [c]	Q_{gs}			-	17	-	
Gate-drain charge [c]	Q_{gd}			-	17	-	
Gate resistance	R_g	f = 1 MHz		0.8	1.7	2.6	Ω
Turn-on delay time [c]	$t_{d(on)}$	V_{DD} = 20 V, R_L = 1.0 Ω, I_D ≅ 20 A, V_{GEN} = 10 V, R_g = 1 Ω		-	17	27	ns
Rise time [c]	t_r			-	19	29	
Turn-off delay time [c]	$t_{d(off)}$			-	30	45	
Fall time [c]	t_f			-	10	15	
Source-Drain Diode Ratings and Characteristics [b]							
Reverse recovery time	t_{rr}	V_{DD} = 32 V, I_{FM} = 15 A, di/dt = 100 A/µs		-	40	80	ns
Reverse recovery charge	Q_{rr}			-	34	68	nC
Reverse recovery current	I_{RM}			-	-1.5	-	A
Pulsed current [a]	I_{SM}			-	-	660	A
Forward voltage	V_{SD}	I_F = 50 A, V_{GS} = 0		-	0.8	1.1	V

Notes

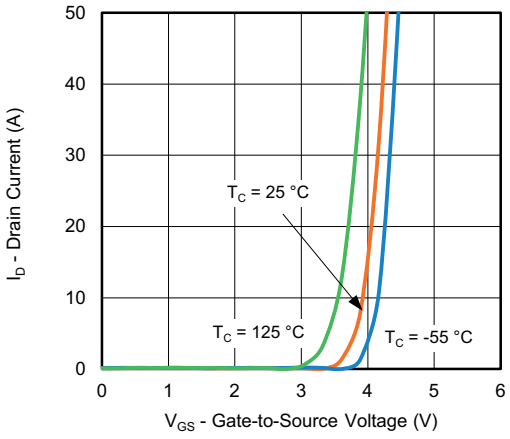
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %
b. Guaranteed by design, not subject to production testing
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

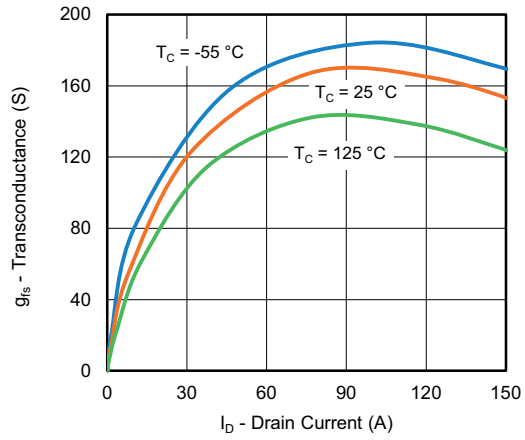
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



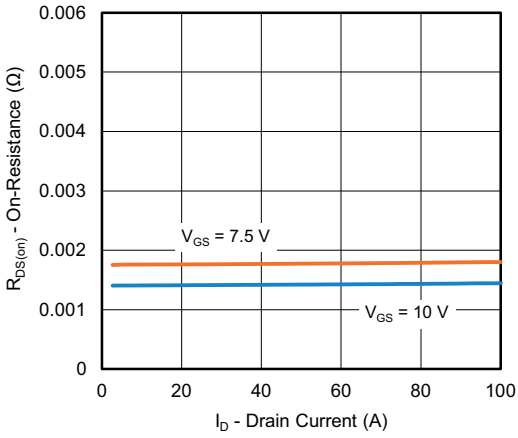
Output Characteristics



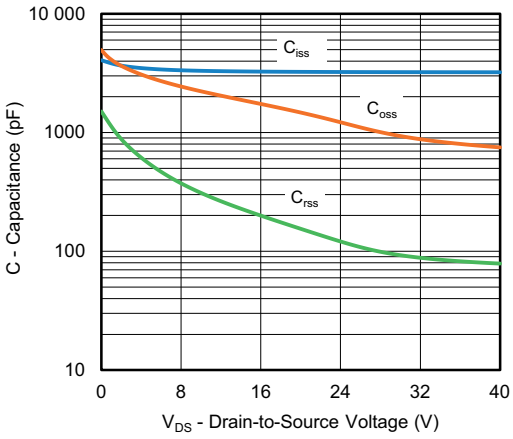
Transfer Characteristics



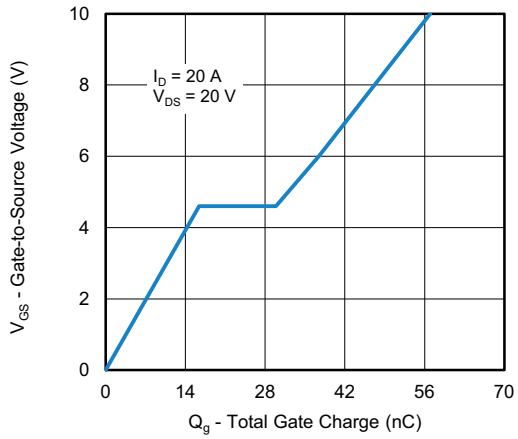
Transconductance



On-Resistance vs. Drain Current

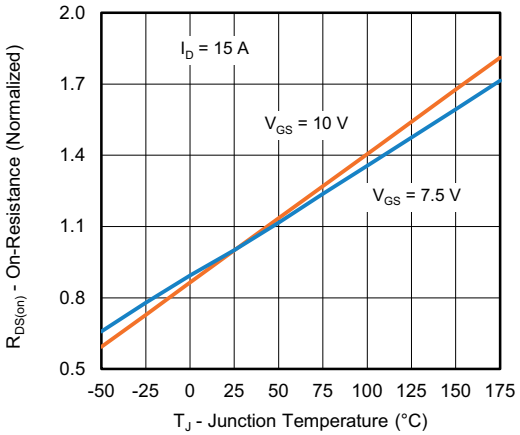


Capacitance

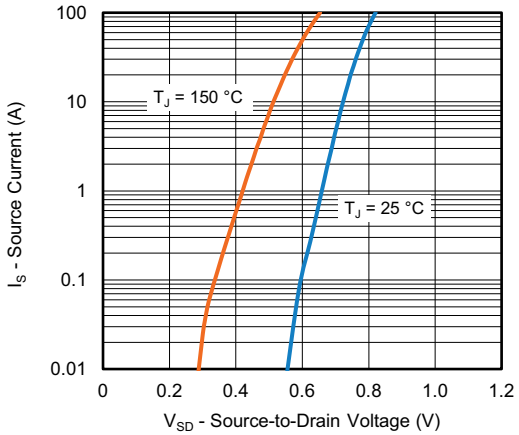


Gate Charge

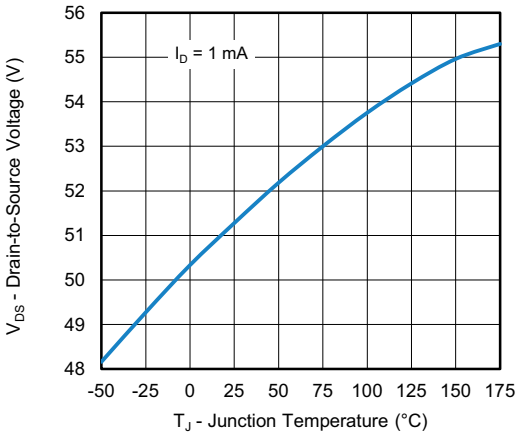
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



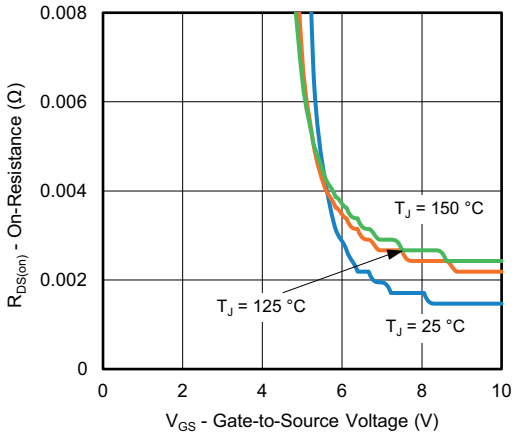
On-Resistance vs. Junction Temperature



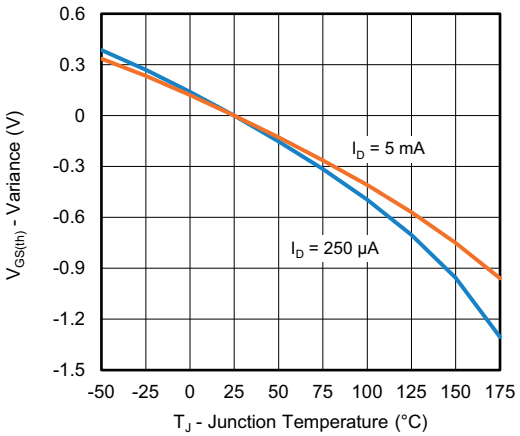
Source Drain Diode Forward Voltage



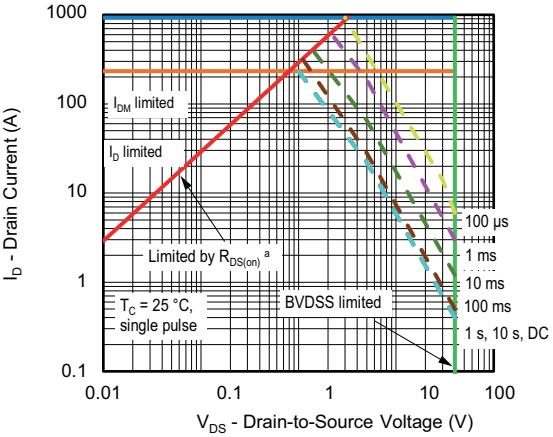
Drain Source Breakdown vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

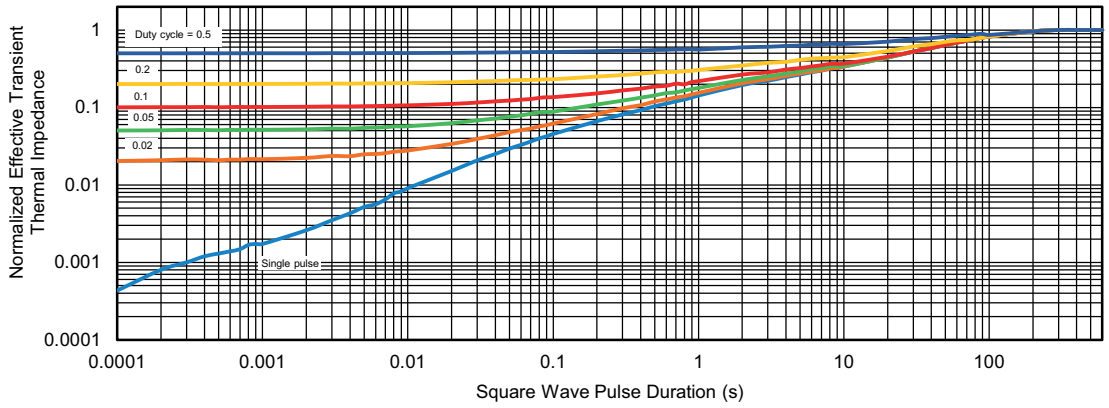


Safe Operating Area

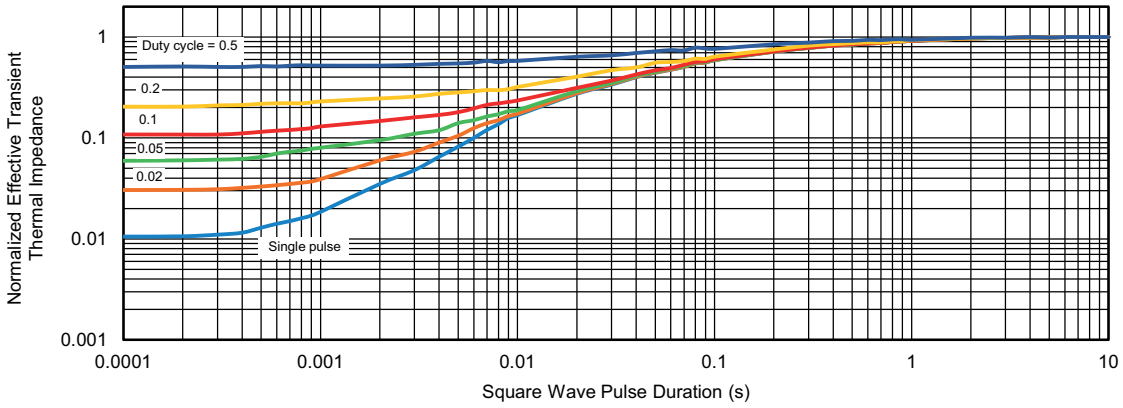
Note

a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



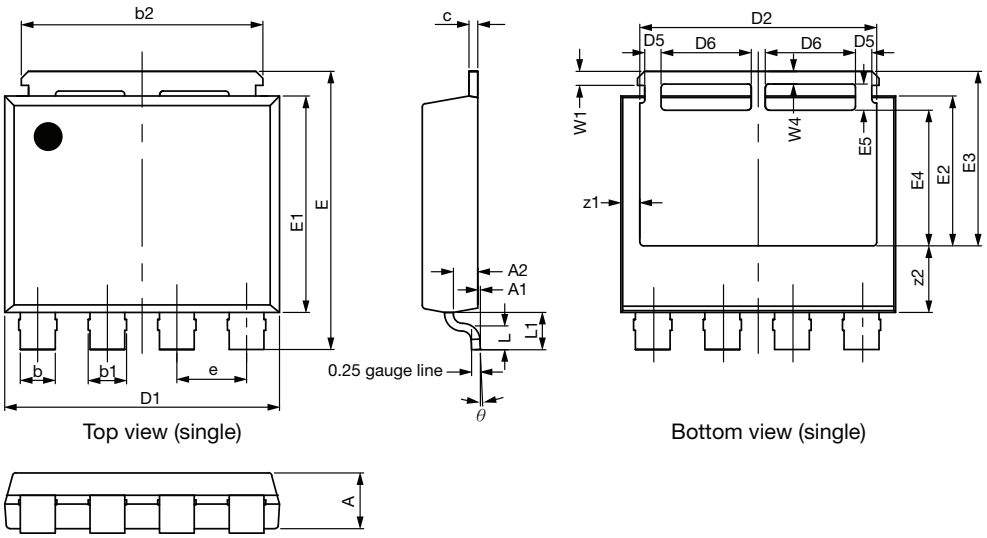
Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?77649.

PowerPAK® 8 x 8L BWL Case Outline 2



Top view (single)

Bottom view (single)

DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	1.50	1.60	1.70	0.059	0.063	0.067
A1	0.00	-	0.127	0.000	-	0.005
A2	0.655	0.705	0.755	0.026	0.028	0.030
b	0.92	1.00	1.08	0.036	0.039	0.043
b1	1.02	1.10	1.18	0.040	0.043	0.046
b2	6.84	6.94	7.04	0.269	0.273	0.277
c	0.20	0.25	0.30	0.008	0.010	0.012
D1	7.80	7.90	8.00	0.307	0.311	0.315
D2	6.70	6.80	6.90	0.264	0.268	0.272
D5	0.37	0.47	0.57	0.015	0.019	0.022
D6	2.49	2.59	2.69	0.098	0.102	0.106
e	1.97	2.00	2.03	0.078	0.079	0.080
E	7.90	8.00	8.10	0.311	0.315	0.319
E1	6.12	6.22	6.32	0.241	0.245	0.249
E2	4.21	4.31	4.41	0.166	0.170	0.174
E3	4.92	5.02	5.12	0.194	0.198	0.202
E4	3.80	3.90	4.00	0.150	0.154	0.157
E5	0.65	0.75	0.85	0.026	0.030	0.033
L	0.61	0.68	0.75	0.024	0.027	0.030
L1	1.00	1.07	1.15	0.039	0.042	0.045
W1	0.30	0.40	0.50	0.012	0.016	0.020
W4	0.32	0.37	0.42	0.013	0.015	0.017
z1	0.45	0.55	0.65	0.018	0.022	0.026
z2	1.81	1.91	2.01	0.071	0.075	0.079
θ	0°	-	5°	0°	-	5°
ECN: S19-0643-Rev. B, 05-Aug-2019 DWG: 6073						

Note

- Millimeter will govern

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